

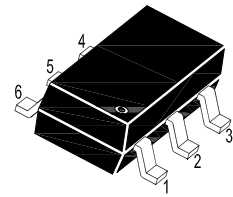
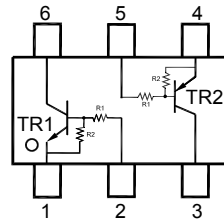
MMDTX436DW

NPN/PNP Silicon Epitaxial Planar Digital Transistor

for switching and interface circuit and drivecircuit applications

Features

- Transistors with different polarity and built-in bias resistors R1 and R2
- Simplification of circuit design
- Reduces number of components and board space



1. Emitter 2. Base 3. Collector
4. Emitter 5. Base 6. Collector
SOT-363 Plastic Package

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$ (TR1)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$ (TR2)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$ (TR1 and TR2)

Parameter	Symbol	Value	Unit
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

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Characteristics at $T_a = 25^\circ\text{C}$ (TR1:NPN)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	h_{FE}	80	-	-	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 50\text{ V}$	I_{CEO}	-	-	500	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	0.074	-	0.138	mA
Collector Emitter Saturation Voltage at $I_C = 5\text{ mA}$, $I_B = 0.25\text{ mA}$	V_{CEsat}	-	-	0.3	V
Input Voltage (OFF) at $V_{CE} = 5\text{ V}$, $I_C = 100\text{ }\mu\text{A}$	$V_{I(OFF)}$	0.5	-	0.8	V
Input Voltage (ON) at $V_{CE} = 0.2\text{ V}$, $I_C = 5\text{ mA}$	$V_{I(ON)}$	0.7	-	1.3	V
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 5\text{ mA}$	f_T	-	250	-	MHz
Collector output capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	Cob	-	-	6	pF

Characteristics at $T_a = 25^\circ\text{C}$ (TR2:PNP)

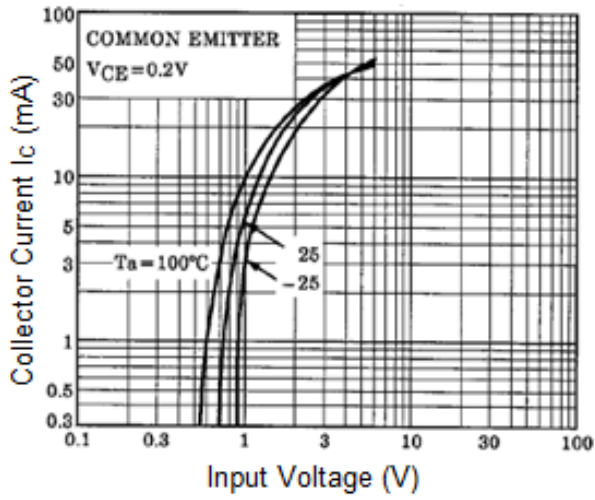
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	h_{FE}	80	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	-	100	nA
Collector Emitter Cutoff Current at $-V_{CE} = 50\text{ V}$	$-I_{CEO}$	-	-	500	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	0.074	-	0.138	mA
Collector Emitter Saturation Voltage at $-I_C = 5\text{ mA}$, $-I_B = 0.25\text{ mA}$	$-V_{CEsat}$	-	-	0.3	V
Input Voltage (OFF) at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ }\mu\text{A}$	$-V_{I(OFF)}$	0.5	-	0.8	V
Input Voltage (ON) at $-V_{CE} = 0.2\text{ V}$, $-I_C = 5\text{ mA}$	$-V_{I(ON)}$	0.7	-	1.3	V
Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 5\text{ mA}$	f_T	-	200	-	MHz
Collector output capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	Cob	-	-	6	pF

Characteristics at $T_a = 25^\circ\text{C}$ (TR1 and TR2)

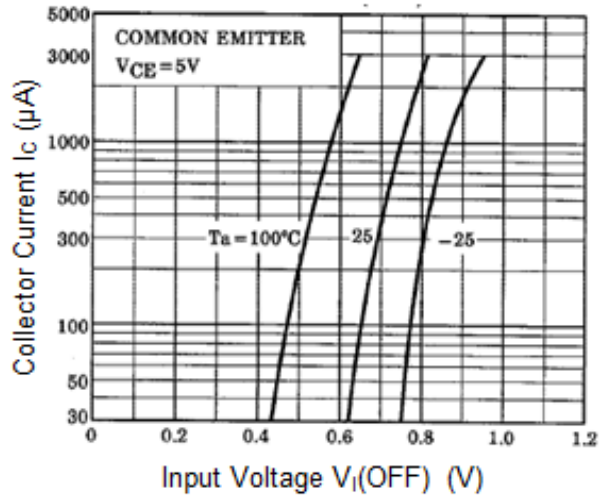
Input Resistance	R_1	3.29	4.7	6.11	K Ω
Resistance Ratio	R_1/R_2	0.09	0.1	0.11	-

TR1

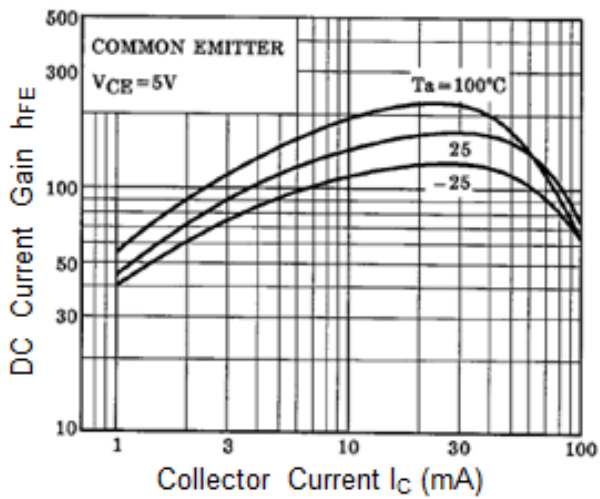
I_C - V_I (ON)



I_C - V_I (OFF)



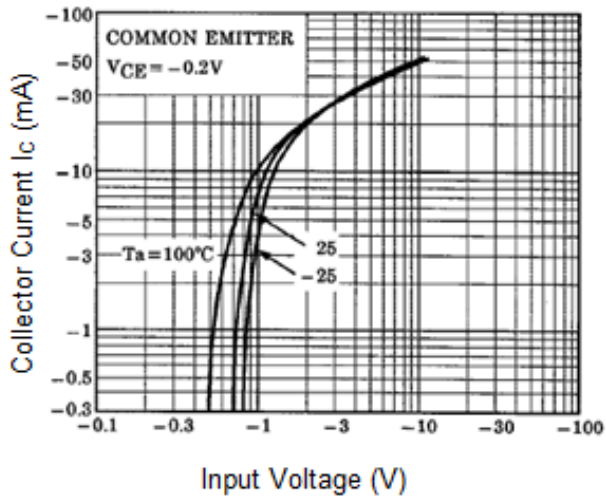
h_{FE} - I_C



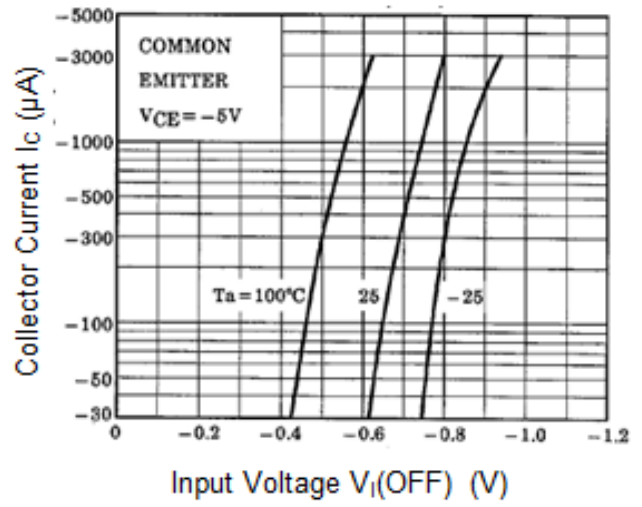
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TR2

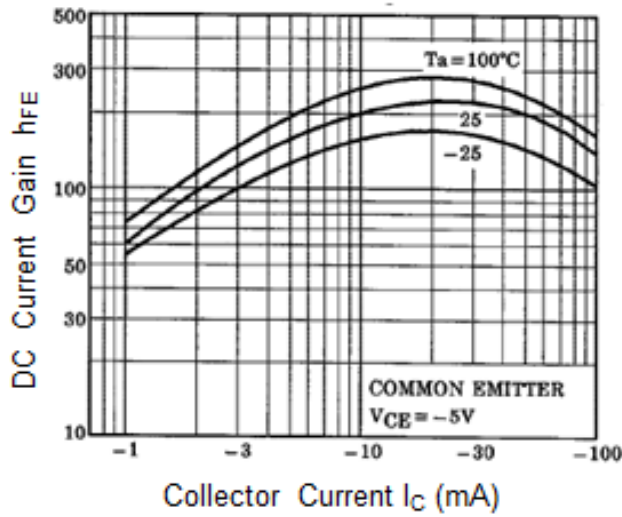
I_C-V_I (ON)



I_C-V_I (OFF)



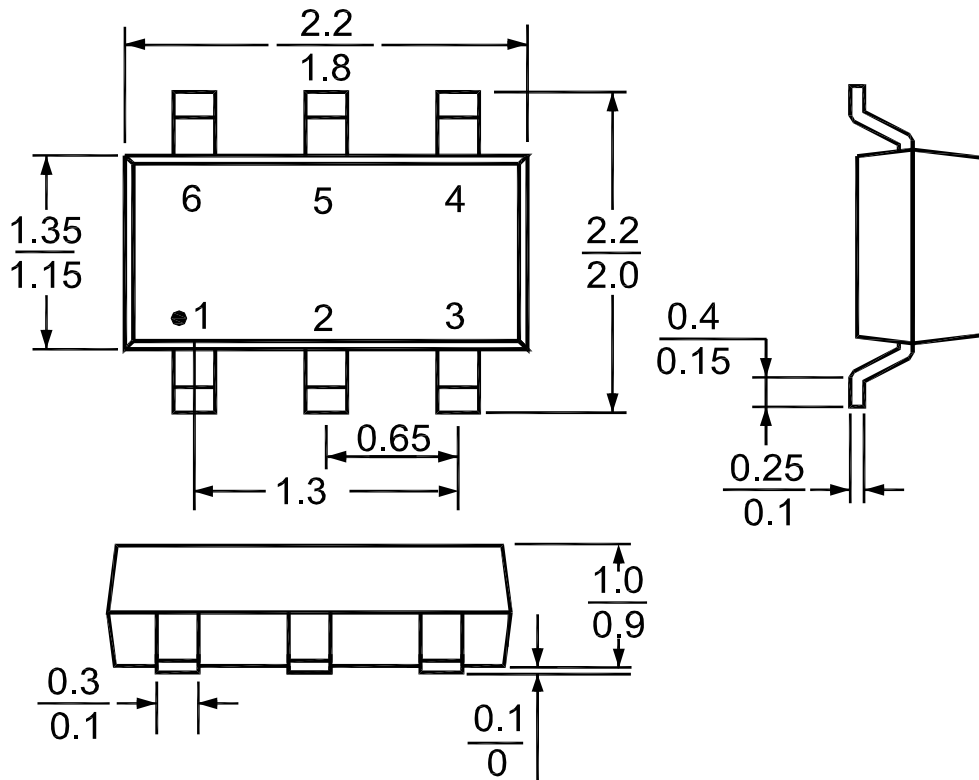
$h_{FE}-I_C$



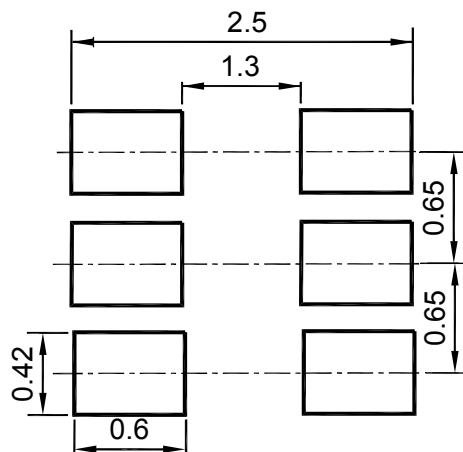
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SOT-363 Package Outline Dimensions (Units: mm)



Recommended Soldering Footprint



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